



PRODUCT BULLETIN #20811

Generic Copy

Issue Date: 09-Mar-2015

TITLE: NCV8876 Datasheet Update

PROPOSED FIRST SHIP DATE: 09-Mar-2015

AFFECTED CHANGE CATEGORY(S): Datasheet Change

FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:

Contact your local ON Semiconductor sales office or Bill Fontes <bill.fontes@onsemi.com>

NOTIFICATION TYPE: Product Bulletin

ON Semiconductor considers this change approved unless specific conditions of acceptance are provided in writing. To do so, contact <quality@onsemi.com>.

DESCRIPTION AND PURPOSE:

A good design practice recommendation of a MOSFET gate-source resistor on the PCB has been added to the datasheet. This resistor prevents the MOSFET from turning on in case of a floating gate.

The recommended resistor has been added to the application drawing on page 2, and a comment is added in the pin description. See below for highlighted changes to page 2.

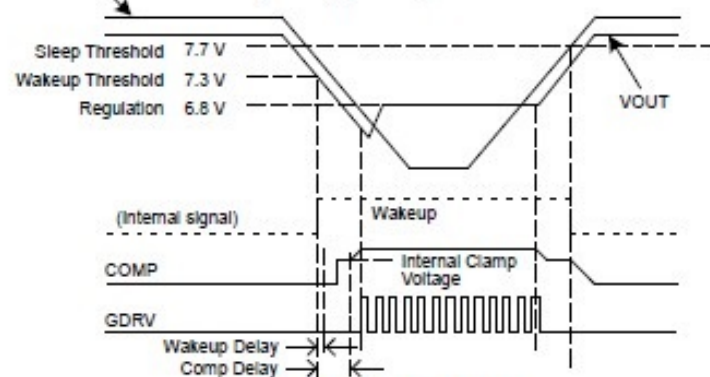
Similar changes made to drawings on pages 8 and 11, and text on pages 5 and 9.

List of Affected General Parts:

NCV887600D1R2G
NCV887601D1R2G

[illegible]

Battery In \



PACKAGE PIN DESCRIPTIONS

Pin No.	Pin Symbol	Function
1	STATUS	This is an open-drain diagnostic. IC status operation flag indicator. This output is a logic low when IC VOUT is below 7.3 V and device is active. A pull-up resistor of around 80 kΩ should be connected between STATUS and a microcontroller reference. This output is a logic high when the IC is disabled or in UVLO.
2	ISNS	Current sense input. Connect this pin to the source of the external N-MOSFET, through a current-sense resistor to ground to sense the switching current for regulation and current limiting.
3	GND	Ground reference.
4	GDRV	Gate driver output. Connect to gate of the external N-MOSFET. A series resistance can be added from GDRV to the gate to tailor EMC performance. An $R_{GND} = 15\text{ k}\Omega$ GDRV-GND resistor is strongly recommended.